

PATENT

AMENDMENTS TO THE SPECIFICATION

Please amend the title in all instances as follows:

BIPOLAR TRANSISTOR WITH AN ULTRA SMALL SELF-ALIGNED POLYSILICON
~~EMITTER AND METHOD OF FORMING THE SILICON GERMANIUM BASE OF THE~~
TRANSISTOR

Please amend the first paragraph on page 1 as follows:

*E.V.
10-1-05*
~~The present application~~ This is a divisional application of Application Serial No.
09/994,293 filed on November 26, 2001, *now patent No. 6,759,234* which is a continuation-in-part of
Application Serial No. 09/882,740 filed June 15, 2001 by Abdalla Aly Naem for
Bipolar Transistor with a Silicon Germanium Base and an Ultra Small Self-Aligned
Polysilicon Emitter and Method of Forming the Transistor, *now patent NO. 6,649,482.*